

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1713	257/355.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/10 10:19
S1	0	electro\$static adj discharge same scr same asymmetric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/03 17:08
S2	431	electro\$static adj discharge same scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/03 17:14
S3	901	(esd electro\$static adj discharge) same (scr silicon adj controlled adj rectifier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 10:12
S4	3	(esd electro\$static adj discharge) same (scr silicon adj controlled adj rectifier) same asymmetric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/03 17:16
S5	8	(esd electro\$static adj discharge) same (scr silicon adj controlled adj rectifier) and asymmetric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/03 17:16
S6	22	scr and wu.in. and (taiwan adj semiconductor).as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/03 17:22
S7	16	(esd electro\$static adj discharge) same (scr silicon adj controlled adj rectifier) same (NFET NMOS) same (PFET PMOS) same buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 10:57

S8	32	("4734752"   "5019888"   "5218222"   "5270565"   "5329143"   "5600525").PN. OR ("5754381"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 10:24
S9	19	("5528188"   "5530612"   "5572394"   "5740000"   "5754381"   "5886862"   "5907464"   "5917336"   "5945713"   "5959820"   "6002568"   "6008684"   "6011681"   "6043539").PN. OR ("6671153").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 10:30
S10	7	("5754381"   "5856214"   "5872379"   "5907462"   "5939756"   "5959820").PN. OR ("6576934"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 10:48
S11	21	("5400202"   "5465189"   "5576557"   "5745323"   "5754380"   "5754381"   "5869873"   "5898205").PN. OR ("6066879"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 10:51
S12	28	(esd electrostatic adj discharge) same (scr silicon adj controlled adj rectifier) same (NFET NMOS) same (PFET PMOS) and diode near (chain string)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 11:06
S13	9	10/099600	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 11:06
S14	35	("5272097"   "5272371"   "5327319"   "5400202"   "5426322"   "5430595"   "5452171"   "5465189"   "5550699"   "5561577"   "5591661"   "5610425"   "5625522"   "5671111"   "5728612"   "5754380"   "5780905"   "5781388"   "5821572"   "5843813"   "5869873"   "5872378"   "5877927"   "5907462"   "5959488"   "5959821"   "5978192"   "5982601"   "6002567"   "6069782"   "6125021"   "6157530"   "6233130"   "6304127"   "6411485").PN. OR ("6768616"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 11:11
S15	10	("5311391").PN. OR ("5550699"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 11:25

S16	38	("4922371"   "5225702"   "5274262"   "5287241").PN. OR ("5430595").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 14:41
S17	1	10/812378	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 14:41
S18	59	asymmetric near (nmos nfet pmos pfet fet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:31
S19	1	asymmetric near (nmos nfet pmos pfet fet) and (scr silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:14
S20	305	asymmetric near (nmos nfet pmos pfet fet transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:15
S21	2	asymmetric near (nmos nfet pmos pfet fet transistor) and (scr silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:16
S22	18	"5905288"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:31
S23	0	"5905288.pn."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:32
S24	2	"5905288".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:45

S25	2	"6768616".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 15:45
S26	35	("5272097"   "5272371"   "5327319"   "5400202"   "5426322"   "5430595"   "5452171"   "5465189"   "5550699"   "5561577"   "5591661"   "5610425"   "5625522"   "5671111"   "5728612"   "5754380"   "5780905"   "5781388"   "5821572"   "5843813"   "5869873"   "5872378"   "5877927"   "5907462"   "5959488"   "5959821"   "5978192"   "5982601"   "6002567"   "6069782"   "6125021"   "6157530"   "6233130"   "6304127"   "6411485").PN. OR ("6768616"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 15:49
S27	13	mergens.in. and sarnoff.as.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 15:50
S28	17	diode adj (string chain) same bias same scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:13
S29	1133910	lateral scr.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 16:57
S30	14	(lateral adj scr).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 16:57
S31	17	diode adj (string chain) same bias same nmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:13

S32	18	diode adj (string chain) same bias same (nmos nfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:19
S33	9	diode adj (string chain) same bias same (mos fet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:20
S34	12	("3501591"   "3886321"   "3927266"   "3953682"   "4099032"   "4158752"   "4360709").PN. OR ("4439634").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 17:20
S35	837	diode adj (string chain) and (scr silicon controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:20
S36	32	diode adj (string chain) same \$1fet and (scr silicon controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:21
S37	3972858	diode adj (string chain) same sourceand (scr silicon controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:21
S38	256	diode adj (string chain) same source and (scr silicon controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:21
S39	72	diode adj (string chain) same source same (scr silicon controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:25
S40	61392	diode adj (string chain) same source (scr silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:25

S41	17	diode adj (string chain) same source same (scr silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:28
S42	378	diode adj (string chain) same source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:36
S43	1	"6768616".pn. and holding same chain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/07 10:03
S44	12	source same holding same diode adj (chain string)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 17:52
S45	14	("3335360"   "3506852"   "3577177"   "3848140"   "3917962").PN. OR ("4024457").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/06 17:49
S46	42	holding adj voltage and diode adj (chain string) and (scr silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 18:08
S47	44	holding adj voltage and diode adj (chain string stack) and (scr silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 18:08
S48	284	holding adj voltage and scr and diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:03
S49	105	holding adj voltage same scr same diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:11

S50	37	holding adj voltage same scr same diode same latch\$1up	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:16
S51	408	output adj buffer and diode adj (chain string stack series)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:17
S52	13	output adj buffer and diode adj (chain string stack series) and scr and holding adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:22
S53	21	buffer and diode adj (chain string stack series) and scr and holding adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:26
S54	177	buffer same diode adj (chain string stack series)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:26
S55	10	buffer same diode adj (chain string stack series) and (scr and silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:31
S56	2180	(WU LEE).IN. AND (taiwan adj semiconductor).as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:32
S57	86	(WU LEE).IN. AND (taiwan adj semiconductor).as. and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:23

S58	18	(WU LEE).IN. AND (taiwan adj semiconductor).as. and diode adj (chain string series stack)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:33
S59	2336	diode adj (chain sereies stack string) (taiwan adj semiconductor).as. and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:41
S60	17	diode adj (chain sereies stack string) and (taiwan adj semiconductor).as. and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:47
S61	84	diode adj (chain sereies stack string) and latch\$1up and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:47
S62	41	diode adj (chain sereies stack string) and latch\$1up and esd and holding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:39
S63	6	10/099263	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 10:58
S64	68	buffer same diode adj (chain string stack series) same source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:46
S65	2	"6768616".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 11:08



S66	0	sarnoff.in. and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 11:09
S67	54	sarnoff.as. and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 11:09
S68	40	("4392781"   "4400711"   "4405933"   "4484244"   "4631567"   "4633283"   "4757363"   "4760433"   "4811155"   "4855620"   "4870530"   "4928157").PN. OR ("5010380").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 11:12
S69	18	("3806773"   "4476476"   "4686602"   "4763184"   "4870530"   "4937471"   "5010380"   "5060037"   "5343053"   "5349212"   "5465189"   "5548134"   "5610426"   "5780905"   "5814865"   "5895940"   "6013941"   "6064093").PN. OR ("6825504"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 11:13
S70	14	("4870530"   "5400202"   "5602404").PN. OR ("5780905"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 11:15
S71	18	("3806773"   "4476476"   "4686602"   "4763184"   "4870530"   "4937471"   "5010380"   "5060037"   "5343053"   "5349212"   "5465189"   "5548134"   "5610426"   "5780905"   "5814865"   "5895940"   "6013941"   "6064093").PN. OR ("6825504"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 11:17
S72	13	("4071779"   "4302792"   "4439802"   "4484244"   "4567500").PN. OR ("4686602"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 11:20
S73	18	("3806773"   "4476476"   "4686602"   "4763184"   "4870530"   "4937471"   "5010380"   "5060037"   "5343053"   "5349212"   "5465189"   "5548134"   "5610426"   "5780905"   "5814865"   "5895940"   "6013941"   "6064093").PN. OR ("6825504"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:39

S74	1	"4825174".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:41
S75	120	(silicon adj controlled) and buffer same source same diode	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:42
S76	18	(silicon adj controlled) and buffer same source same diode same holding	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:43
S77	18	(silicon adj controlled) and buffer same source same diode\$1 same holding	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:43
S78	18	(silicon adj controlled) and buffer same (source drain) same diode\$1 same holding	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:45
S79	32	(silicon adj controlled) and buffer same diode\$1 same holding	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:48
S80	50	(silicon adj controlled) and (nmos nfet) with diode\$1 and holding	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:56
S81	15	Chartered.as. and scr	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:58
S82	37	Chartered.as. and esd	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:58
S83	15	("4037164"   "5528190"   "5576557"   "5631793"   "5895940"   "5905288"   "5986862"   "6008974"   "6130811").PN. OR ("6275089").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 16:04
S84	19	("5077591"   "5225702"   "5274262"   "5453384"   "5465189"   "5473169"   "5485024"   "5493133"   "5500546"   "5506742").PN. OR ("5821572"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 16:37
S85	124	diode adj (chain series stack string) and latch\$1up and esd and holding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:39
S86	12	diode adj (chain series stack string) with holding and latch\$1up and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:44

S87	13	("5959820"   "6015992").PN. OR ("6521952").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 16:42
S88	0	diode adj (chain series stack string) with holding same latch\$1up same buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:45
S89	1	diode adj (chain series stack string) same holding same latch\$1up same buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:45
S90	3	diode adj (chain series stack string) same buffer and holding same latch\$1up	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:45
S91	1	buffer same diode adj (chain string stack series) same (latch\$1up latch adj up)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 16:47
S92	10	buffer same diode adj (chain string stack series) and (latch\$1up latch adj up)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:02
S93	21	thick adj field adj oxide adj device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:08
S94	2492	(\$1mos \$1fet) with source with drain with gate with diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:09
S95	73	(\$1mos \$1fet) with source with drain with gate with diode same buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:09

S96	0	(\$1mos \$1fet) with source with drain with gate with diode same buffer same holding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:09
S97	0	(\$1mos \$1fet) with source with drain with gate with diode same buffer same scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:09
S98	0	(\$1mos \$1fet) with source with drain with gate with diode same buffer same \$3scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:09
S99	73	(\$1mos \$1fet) with source with drain with gate with diode same buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:10
S10 0	0	(\$1mos \$1fet) with source with drain with gate with diode same buffer and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:10
S10 1	4	(\$1mos \$1fet) with source with drain with gate with diode same buffer and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:13
S10 2	2	"4767946".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/07 17:13
S10 3	17	("4456838"   "4578602"   "4644194").PN. OR ("4767946").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 17:16
S10 4	9	("4612514"   "4616189"   "4634993"   "4646028"   "4767946").PN. OR ("4825174").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 17:23
S10 5	36	buffer with diode adj (chain series string stack)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 17:40

S10 6	990	hold\$3 same (silicon adj controlled) same (chain string series stack)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 17:47
S10 7	20	hold\$3 same (silicon adj controlled) same diode adj (chain string series stack)	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 17:42
S10 8	8	hold\$3 same (silicon adj controlled) same (chain string series stack) and nmos	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 17:54
S10 9	1	"4825174".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 17:54
S11 0	320	scr and esd and latch\$1up	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 11:10
S11 1	99	scr same holding same latch\$1up	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 11:32
S11 2	2	10/062714	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 11:32
S11 3	30	("20020084490"   "20030007301"   "4939616"   "5012317"   "5225702"   "5453384"   "5465189"   "5502328"   "5519242"   "5581104"   "5629544"   "5631793"   "5646808"   "5654862"   "5719737"   "5754381"   "5807791"   "5811857"   "5824573"   "5907462"   "5910874"   "5932918"   "5940258"   "5990520"   "6015992"   "6034397"   "6081002"   "6242763"   "6521952").PN. OR ("6750515").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/08 11:32
S11 4	1	10/812378	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 12:26

S11 5	2	"5905288".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 12:27
S11 6	2	"6521952".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 12:41
S11 7	273	snap\$1back and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 12:42
S11 8	91	snap\$1back and scr and speed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 12:42
S11 9	2	snap\$1back same speed same scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 12:42
S12 0	4	(taiwan adj semiconductor).as. and scr same speed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 13:53
S12 1	2	beta adj gain with capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 13:54
S12 2	5	beta adj gain with scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 13:57

S12 3	11	beta adj gain same scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 13:59
S12 4	356	beta same scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 13:59
S12 5	4	beta same scr same capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:00
S12 6	32	beta same scr same increase	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:38
S12 7	137	asymmetric\$3 near transistors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:39
S12 8	1	asymmetric\$3 near transistors and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:39
S12 9	137	asymmetric\$3 near transistors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:39
S13 0	0	asymmetric\$3 near transistors and ker .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:40

S13 1	0	asymmetric\$3 near transistors and ker.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:40
S13 2	5	asymmetric\$3 near transistors and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 14:40
S13 3	95	ker.in. and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 15:06
S13 4	201	scr and guard adj ring	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:34
S13 5	1156	asymmetric with transistors	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:39
S13 6	11	asymmetric with transistors and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:49
S13 7	72	short adj channel adj NMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:51
S13 8	23	short adj channel adj NMOS and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:52



S13 9	1	asymmetric\$3 adj (NMOS NFET transistor\$1)and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:54
S14 0	1	asymmetric\$3 adj (NMOS NFET transistor\$1) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:54
S14 1	1	asymm\$6 adj (NMOS NFET transistor\$1) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 15:54
S14 2	76	asymm\$6 same (NMOS NFET transistor\$1) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 16:03
S14 3	6	asymm\$6 with (source and drain) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 16:04
S14 4	11	("20020058373"   "20030034527"   "4939616"   "5012317"   "5369041"   "5465189"   "5907462"   "6081002"   "6303420"   "6548337"   "6639284").PN. OR ("6869840"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/08 16:29
S14 5	4	257/592.ccls. and scr	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/08 16:29
S14 6	6	(257/592 257/593).ccls. and scr	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/08 16:35
S14 7	805	snap\$1back and esd	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/08 16:36
S14 8	311	snap\$1back and esd and buffer	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/08 16:36

S14 9	1	10/812378	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:18
S15 0	582	dual with asymm\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:18
S15 1	24	dual with asymm\$5 same (\$1fet \$1mos transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:22
S15 2	342	(two dual) with asymm\$5 same (\$1fet \$1mos transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:23
S15 3	2	(two dual) with asymm\$5 same (\$1fet \$1mos transistor) same (silicon adj controlled scr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:23
S15 4	4	(two dual) with asymm\$5 same (\$1fet \$1mos transistor) and (silicon adj controlled scr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:24
S15 5	27	(two dual) same asymm\$5 same (\$1fet \$1mos transistor) and (silicon adj controlled scr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:26
S15 6	1	(two dual double) near asymm\$5 same (\$1fet \$1mos transistor) and (silicon adj controlled scr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:26

S15 7	12	(two dual double) near asymm\$5 and (silicon adj controlled scr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:26
S15 8	101	(two dual double) with asymm\$5 and (silicon adj controlled scr)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:27
S15 9	28	(two dual double) with asymm\$5 and (silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:28
S16 0	215	asymm\$5 and (silicon adj controlled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:28
S16 1	14	asymm\$5 and (silicon adj controlled) and esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 11:28
S16 2	325	drain adj extended	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:08
S16 3	16	drain adj extended same scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:12
S16 4	2	"5,903,032".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:15

S16 5	41	denmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:15
S16 6	15	(denmos depmos) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:19
S16 7	20	(demos denmos depmos) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:20
S16 8	0	senmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:20
S16 9	20	semos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:20
S17 0	20	(semos demos denmos depmos) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:32
S17 1	68	(semos demos denmos depmos) and scr	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 12:20
S17 2	10	("5416351"   "5559352"   "5870268"   "5898205"   "5918127"   "6066879").PN. OR ("6444511"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 12:26
S17 3	1	10/278094	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 12:27

S17 4	16	(two dual double) near (semos demos denmos depmos)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 12:35
S17 5	0	parallel near (semos denmos depms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:35
S17 6	9	parallel with (semos denmos depms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 12:36
S17 7	7	second with (semos denmos depms)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 13:26
S17 8	199	second with (semos denmos depms drain adj extend\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 13:27
S17 9	21	dual with (semos denmos depms drain adj extend\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/09 13:27
S18 0	33	("5276371"   "5374565"   "5438213"   "5455436"   "5508548"   "5515226"   "5548134"   "5576570"   "5674761"   "5707886"   "5897348"   "5953606"   "5994176"   "5998245"   "6004838"   "6022769").PN. OR ("6143594"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 13:31
S18 1	25	("5516717"   "5529941"   "5554544"   "5585299"   "5618740"   "5672527"   "5877048"   "5897348"   "5905284"   "5910672"   "5917218"   "5920774").PN. OR ("5994176").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 13:42
S18 2	423645	dual gate and scr	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 13:43

S18 3	28	dual adj gate and scr	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:01
S18 4	1	"5,455,436".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:01
S18 5	35	("5182220"   "5225702").PN. OR ("5455436").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:04
S18 6	14	("20020053704"   "5455436"   "5572394"   "5637900"   "5753381"   "5754380"   "5754381"   "5811856"   "5872379"   "5898205"   "6066879").PN. OR ("6661060"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:07
S18 7	21	("5400202"   "5465189"   "5576557"   "5745323"   "5754380"   "5754381"   "5869873"   "5898205").PN. OR ("6066879"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:19
S18 8	1	"5,753,380".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:20
S18 9	1	"5,753,381".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:24
S19 0	26	ker.in. and beta	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:29
S19 1	76	(lee wu).in. and beta and scr	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:30
S19 2	3	(lee wu).in. and beta same double and scr	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:30
S19 3	1652	(lee wu).in. and beta and silicon	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:30
S19 4	31	(lee wu).in. and beta and silicon adj controlled	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:43
S19 5	1	"6143594".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:45
S19 6	1	"5,455,436".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:47
S19 7	0	denmos same speed	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:48

S19 8	2	denmos same turn\$1on	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 14:53
S19 9	1	denmos same fast	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 16:39
S20 0	18	"5473169"	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 16:39
S20 1	1	"5473169".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 17:16
S20 2	1	"6066879".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/09 17:16